

< HV MOSFET MODULE >

FMF400DC-66BEW

HIGH POWER SWITCHING USE

INSULATED TYPE

2nd gen. HV MOSFET (High Voltage Metal Oxide Semiconductor Field Effect Transistor) Modules

FMF400DC-66BEW



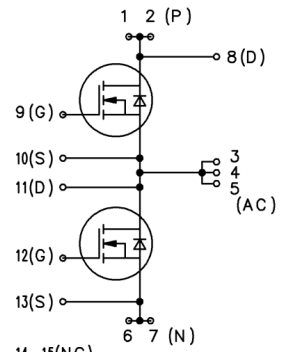
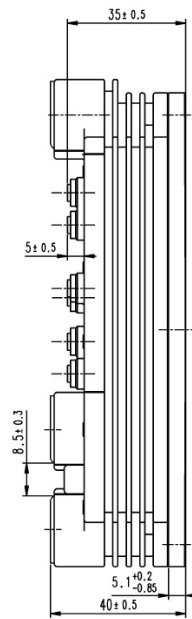
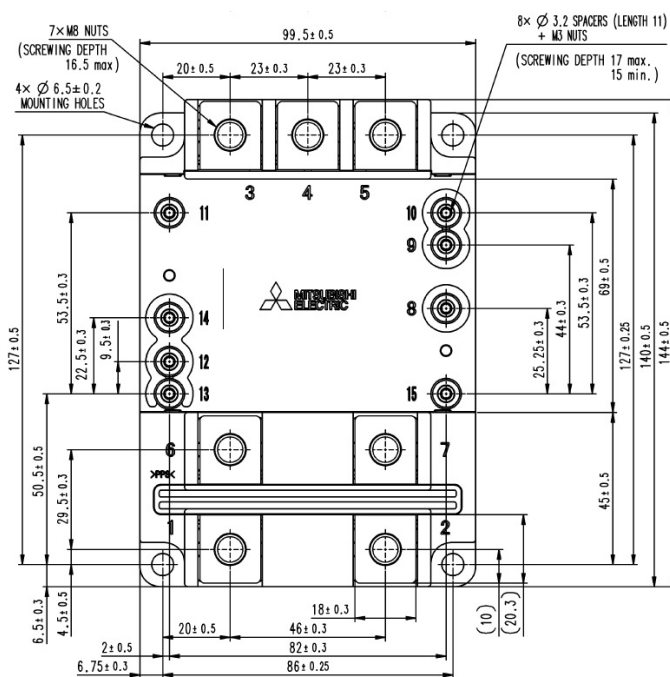
- I_D 400 A
- V_{DSX} 3300 V
- 2-elements in a Pack
- Insulated Type
- SiC SBD embedded MOSFET

APPLICATION

Traction drives, High Reliability Converters / Inverters, DC choppers

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



CIRCUIT DIAGRAM

No.	Terminals
1, 2	DC+, D(P)
3, 4, 5	AC, S(P), D(N)
6, 7	DC-, S(N)
8	D(P)
9	G(P)
10	S(P)
11	D(N)
12	G(N)
13	S(N)
14, 15	NC

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MAXIMUM RATINGS

Item	Symbol	Condition	Ratings	Unit	
Drain-Source voltage, specified gate-source voltage	V_{DSX}	$V_{GS} = -7 V$	$T_J = -40 \sim 175 \text{ }^\circ\text{C}$	3300	V
Gate-Source voltage	V_{GSS}	$V_{DS} = 0 V$	$T_J = -40 \sim 175 \text{ }^\circ\text{C}$	± 20	V
Drain current	I_D	$V_{GS} = 17 V, T_c = 105 \text{ }^\circ\text{C}$, AC terminal output current (Note 1)		400	A
Drain current	I_{DP}	Non repetitive pulse	$T_J = T_{op}$	800	A
Reverse drain current (FWD forward current)	I_S	$V_{GS} = -7 V, T_c = 103 \text{ }^\circ\text{C}$, AC terminal output current(Note 1)(Note 2)		400	A
Reverse drain current (FWD forward current)	I_{SP}	Non repetitive pulse(Note 2)	$T_J = T_{op}$	800	A
Total power dissipation	P_{tot}	$T_c = 25 \text{ }^\circ\text{C}$, MOSFET part(Note 3)		4160	W
Isolation voltage	V_{isol}	Charge part to the baseplate RMS sinusoidal, 60Hz 1min		6000	V_{rms}
Partial discharge charge	Q_{pd}	Charged part to the baseplate RMS sinusoidal, 60 Hz 1min V1 = 3500 V, V2 = 2600 V(acc. to IEC 61287-1)		10	pC
Junction temperature	T_J	Maximum temperature range in off-state or on-state(non-switching)		-40~175	$^\circ\text{C}$
Case temperature	T_c	Maximum case temperature range in on-state		-40~150	$^\circ\text{C}$
Storage temperature	T_{stg}	Maximum case temperature range in off-state		-50~175	$^\circ\text{C}$
Operating junction temperature	T_{Jop}	Maximum junction temperature range for switching operation		-40~175	$^\circ\text{C}$
Short-circuit withstand pulse duration	t_{psc}	$V_{DD} = 2500 V, V_{GS} = +17 / -7 V, L_s = 40 nH, V_{GS}50\%-V_{GS}50\%$	$T_J = T_{op}$	1.7	μs
Short circuit energy	E_{sc}	$V_{DD} = 2500 V, F(t)_{weibull}=1\%$	$T_J = T_{op}$	17.5	J
Non-repetitive surge forward current	I_{FSM}		$T_J = 175 \text{ }^\circ\text{C}$	2.9	kA
I ² t value	i^2t		$T_J = 175 \text{ }^\circ\text{C}$	43	kA^2s

ELECTRICAL CHARACTERISTICS

Item	Symbol	Condition	Limits			Unit	
			Min.	Typ.	Max.		
Gate-source leakage current	I_{GSS}	$V_{DS} = 0 V, V_{GS} = V_{GSS}$	$T_J = 25 \text{ }^\circ\text{C}$	-1.0	-	1.0	μA
Drain-source cut-off current	I_{DSX}	$V_{DS} = V_{DSX}, V_{GS} = -7 V$	$T_J = 25 \text{ }^\circ\text{C}$	-	0.002	-	mA
			$T_J = 150 \text{ }^\circ\text{C}$	-	0.025	-	mA
			$T_J = 175 \text{ }^\circ\text{C}$	-	0.040	1.5	mA
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = 10 V, I_D = 40mA$	$T_J = 25 \text{ }^\circ\text{C}$	1.60	2.10	2.60	V
			$T_J = 150 \text{ }^\circ\text{C}$	-	1.50	-	V
			$T_J = 175 \text{ }^\circ\text{C}$	0.90	1.45	1.90	V
Drain-source on resistance	$r_{DS(on)}$	$V_{DS} = V_{DS(on)}, V_{GS} = 17 V$	$T_J = 25 \text{ }^\circ\text{C}$	-	4.00	-	m Ω
			$T_J = 150 \text{ }^\circ\text{C}$	-	8.63	-	m Ω
			$T_J = 175 \text{ }^\circ\text{C}$	-	10.00	12.13	m Ω
Drain-source on-state voltage	$V_{DS(on)}$	$I_D = 400 A, V_{GS} = 17 V, (Note 4)$	$T_J = 25 \text{ }^\circ\text{C}$	-	1.60	-	V
			$T_J = 150 \text{ }^\circ\text{C}$	-	3.45	-	V
			$T_J = 175 \text{ }^\circ\text{C}$	-	4.00	4.85	V
Source-drain voltage	$V_{SD(on)}$	$I_S = 400 A, V_{GS} = 17 V, (Note 4)$	$T_J = 25 \text{ }^\circ\text{C}$	-	1.45	-	V
			$T_J = 150 \text{ }^\circ\text{C}$	-	3.25	-	V
			$T_J = 175 \text{ }^\circ\text{C}$	-	3.80	4.40	V
Source-drain voltage	V_{SD}	$I_S = 400 A, V_{GS} = 0 V, (Note 4)$	$T_J = 25 \text{ }^\circ\text{C}$	-	2.00	-	V
			$T_J = 150 \text{ }^\circ\text{C}$	-	3.85	-	V
			$T_J = 175 \text{ }^\circ\text{C}$	-	4.35	5.00	V
Source-drain voltage	$V_{SD(off)}$	$I_S = 400 A, V_{GS} = -7 V, (Note 4)$	$T_J = 25 \text{ }^\circ\text{C}$	-	2.00	-	V
			$T_J = 150 \text{ }^\circ\text{C}$	-	3.85	-	V
			$T_J = 175 \text{ }^\circ\text{C}$	-	4.35	5.00	V
Input capacitance	C_{iss}	$V_{DS} = 10 V, V_{GS} = 0 V, f = 100kHz, 1/2 \text{ module}$	$T_J = 25 \text{ }^\circ\text{C}$	-	55	-	nF
Output capacitance	C_{oss}	$V_{DS} = 10 V, V_{GS} = 0 V, f = 100kHz, 1/2 \text{ module}$	$T_J = 25 \text{ }^\circ\text{C}$	-	35	-	nF
Reverse transfer capacitance	C_{rss}	$V_{DS} = 10 V, V_{GS} = 0 V, f = 100kHz, 1/2 \text{ module}$	$T_J = 25 \text{ }^\circ\text{C}$	-	1.4	-	nF
Gate charge	Q_G	$V_{DD} = 1800 V, I_D = 400 A, V_{GS} = +17 / -7 V, 1/2 \text{ module}$	$T_J = 25 \text{ }^\circ\text{C}$	-	1.65	-	μC

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ELECTRICAL CHARACTERISTICS

Item	Symbol	Condition	Limits			Unit	
			Min.	Typ.	Max.		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 1800\text{ V}, I_D = 400\text{ A}, V_{GS} = +17 / -7\text{ V}, L_s = 40\text{ nH}$	$T_j = 175\text{ }^\circ\text{C}$	-	-	0.41	μs
Rise time	t_r	$V_{DD} = 1800\text{ V}, I_D = 400\text{ A}, V_{GS} = +17 / -7\text{ V}, L_s = 40\text{ nH}$	$T_j = 175\text{ }^\circ\text{C}$	-	-	0.24	μs
Turn-on (switching) energy per pulse 10% integral	$E_{on(10\%)}$	$V_{DD} = 1800\text{ V}, I_D = 400\text{ A}, V_{GS} = +17 / -7\text{ V}, L_s = 40\text{ nH}$ $R_{G(on)} = 1.5\ \Omega, R_{G(off)} = 3.0\ \Omega, \text{ Inductive load}$	$T_j = 25\text{ }^\circ\text{C}$	-	0.13	-	J
			$T_j = 150\text{ }^\circ\text{C}$	-	0.11	-	J
			$T_j = 175\text{ }^\circ\text{C}$	-	0.11	-	J
Turn-on (switching) energy per pulse	E_{on}	$V_{DD} = 1800\text{ V}, I_D = 400\text{ A}, V_{GS} = +17 / -7\text{ V}, L_s = 40\text{ nH}$ $R_{G(on)} = 1.5\ \Omega, R_{G(off)} = 3.0\ \Omega, \text{ Inductive load}$	$T_j = 25\text{ }^\circ\text{C}$	-	0.14	-	J
			$T_j = 150\text{ }^\circ\text{C}$	-	0.12	-	J
			$T_j = 175\text{ }^\circ\text{C}$	-	0.12	-	J
Total capacitive charge	Q_C	$V_{DD} = 1800\text{ V}, I_D = 400\text{ A}, V_{GS} = +17 / -7\text{ V}, L_s = 40\text{ nH}$ $R_{G(on)} = 1.5\ \Omega, R_{G(off)} = 3.0\ \Omega, \text{ Inductive load}$	$T_j = 25\text{ }^\circ\text{C}$	-	5.4	-	μC
			$T_j = 150\text{ }^\circ\text{C}$	-	6.3	-	μC
			$T_j = 175\text{ }^\circ\text{C}$	-	6.3	-	μC
Diode turn-off energy (per pulse)	$E_{off_Diode(10\%)}$	$V_{DD} = 1800\text{ V}, I_D = 400\text{ A}, V_{GS} = +17 / -7\text{ V}, L_s = 40\text{ nH}$ $R_{G(on)} = 1.5\ \Omega, R_{G(off)} = 3.0\ \Omega, \text{ Inductive load}$	$T_j = 25\text{ }^\circ\text{C}$	-	0.80	-	mJ
			$T_j = 150\text{ }^\circ\text{C}$	-	-	-	mJ
			$T_j = 175\text{ }^\circ\text{C}$	-	1.80	-	mJ
Diode switching off energy of diode	E_{off_Diode}	$V_{DD} = 1800\text{ V}, I_D = 400\text{ A}, V_{GS} = +17 / -7\text{ V}, L_s = 40\text{ nH}$ $R_{G(on)} = 1.5\ \Omega, R_{G(off)} = 3.0\ \Omega, \text{ Inductive load}$	$T_j = 25\text{ }^\circ\text{C}$	-	1.00	-	mJ
			$T_j = 150\text{ }^\circ\text{C}$	-	-	-	mJ
			$T_j = 175\text{ }^\circ\text{C}$	-	2.00	-	mJ
Turn-off delay time	$t_{d(off)}$	$V_{DD} = 1800\text{ V}, I_D = 400\text{ A}, V_{GS} = +17 / -7\text{ V}, L_s = 40\text{ nH}$	$T_j = 175\text{ }^\circ\text{C}$	-	-	0.94	μs
Fall time	t_f	$V_{DD} = 1800\text{ V}, I_D = 400\text{ A}, V_{GS} = +17 / -7\text{ V}, L_s = 40\text{ nH}$	$T_j = 175\text{ }^\circ\text{C}$	-	-	0.40	μs
Turn-off (switching) energy per pulse 10% integral	$E_{off(10\%)}$	$V_{DD} = 1800\text{ V}, I_D = 400\text{ A}, V_{GS} = +17 / -7\text{ V}, L_s = 40\text{ nH}$ $R_{G(on)} = 1.5\ \Omega, R_{G(off)} = 3.0\ \Omega, \text{ Inductive load}$	$T_j = 25\text{ }^\circ\text{C}$	-	0.05	-	J
			$T_j = 150\text{ }^\circ\text{C}$	-	0.06	-	J
			$T_j = 175\text{ }^\circ\text{C}$	-	0.06	-	J
Turn-off (switching) energy per pulse	E_{off}	$V_{DD} = 1800\text{ V}, I_D = 400\text{ A}, V_{GS} = +17 / -7\text{ V}, L_s = 40\text{ nH}$ $R_{G(on)} = 1.5\ \Omega, R_{G(off)} = 3.0\ \Omega, \text{ Inductive load}$	$T_j = 25\text{ }^\circ\text{C}$	-	0.05	-	J
			$T_j = 150\text{ }^\circ\text{C}$	-	0.06	-	J
			$T_j = 175\text{ }^\circ\text{C}$	-	0.06	-	J

THERMAL CHARACTERISTICS

Item	Symbol	Condition	Limits			Unit
			Min.	Typ.	Max.	
Thermal resistance junction to case	$R_{th(j-c)}$	Junction to Case, MOSFET + embeded SBD part, 1/2 module	-	-	36.0	K/kW
Contact thermal resistance case to heatsink	$R_{th(c-s)}$	Case to heat sink, $\lambda_{grease} = 1\text{ W/m}\cdot\text{K}, D_{(c-s)} = 70\ \mu\text{m}, 1/2\ \text{module}$	-	28.5	-	K/kW

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Item	Symbol	Condition	Limits			Unit
			Min.	Typ.	Max.	
Mounting torque	M_t	Main terminal screw M8 This is the case when installing the product on the bus bar	7.0	-	22.0	N·m
Mounting torque	M_t	Mounting screw M6	3.0	-	6.0	N·m
Mounting torque	M_t	Auxiliary terminals screw M3	0.4	-	0.8	N·m
mass	m	-	-	0.8	-	kg
Comparative tracking index	CTI	-	600	-	-	-
Clearance distance in air	d_a	Between main terminal	8.0	-	-	mm
Creepage distance along surface	d_s	-	32.0	-	-	mm
Internal inductance, D-S	L_{PDS}	Between DC+ and DC- (terminal1,2-6,7)	-	17	-	nH
	L_{PDS}	Between DC+ and AC (terminal1,2-3,4,5)	-	45	-	nH
	L_{PDS}	Between AC and DC- (terminal3,4,5-6,7)	-	45	-	nH

Note 1. Control Case Temperature (T_c) so that the junction temperature (T_j) does not exceed the maximum rating.

Note 2. The symbols represent characteristics of the anti-parallel, source to drain free-wheel diode (FWDi).

Note 3. Junction temperature (T_j) should not exceed T_{jmax} rating.

Note 4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

Products falling under the subject item No. 2 (41) 3 of Appended Table 1 of the Export Trade Control Order.

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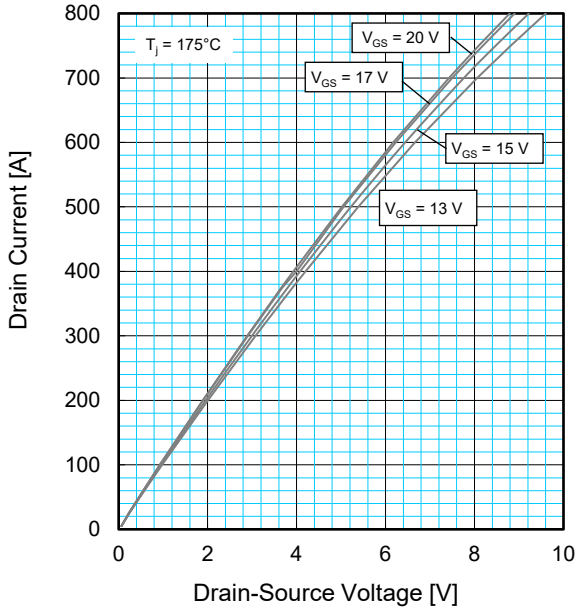
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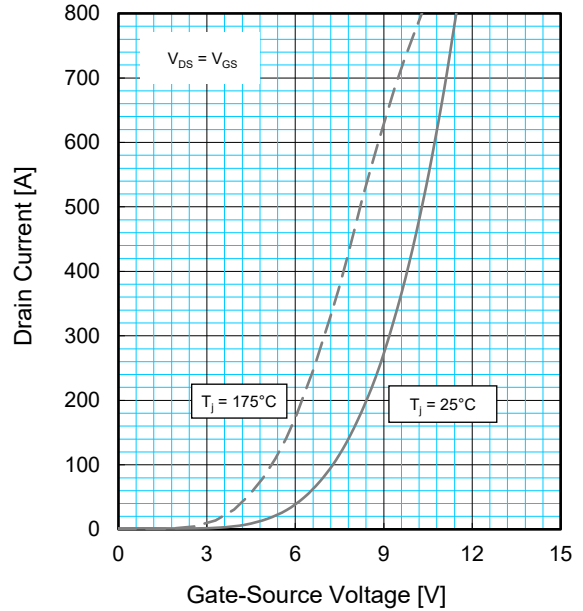
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PERFORMANCE CURVES

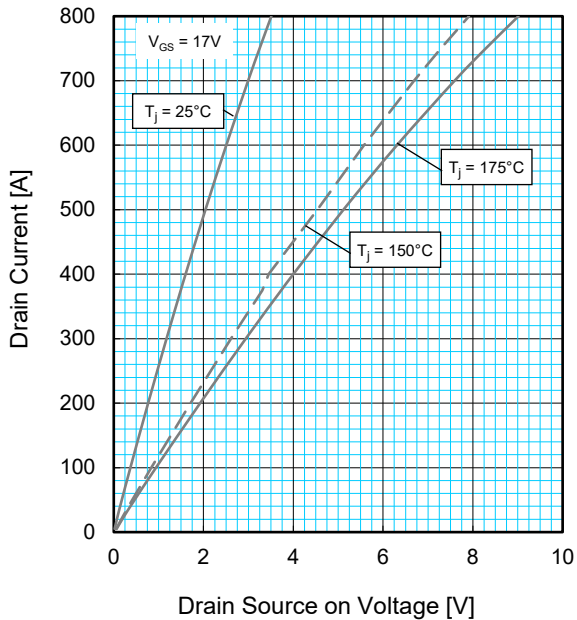
OUTPUT CHARACTERISTICS (TYPICAL)



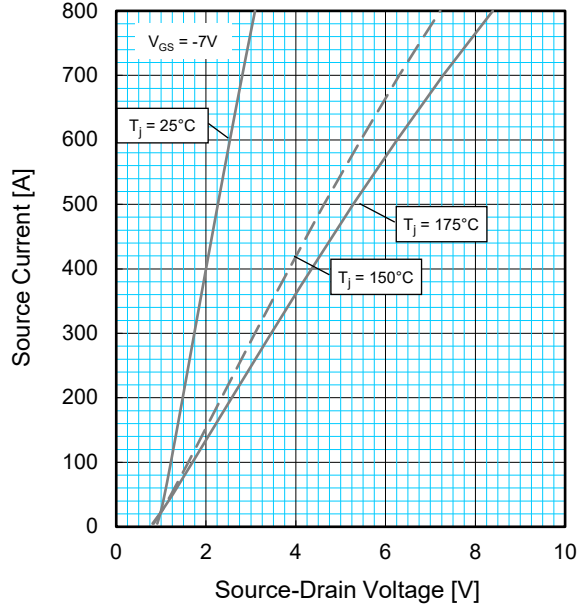
TRANSFER CHARACTERISTICS (TYPICAL)



DRAIN-SOURCE ON VOLTAGE CHARACTERISTICS (TYPICAL)



FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



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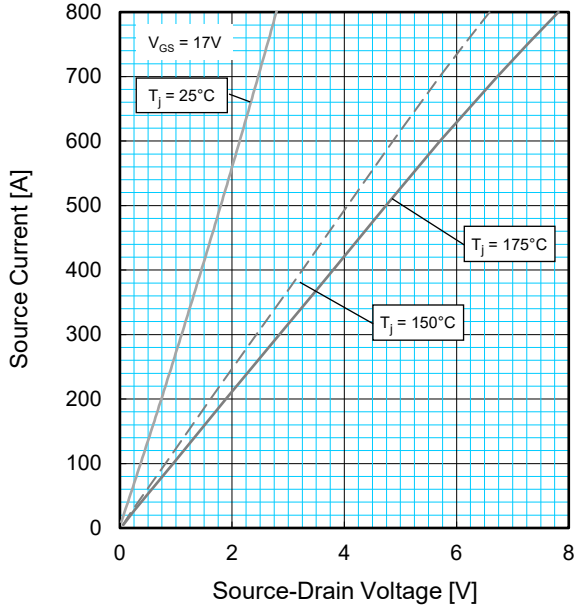
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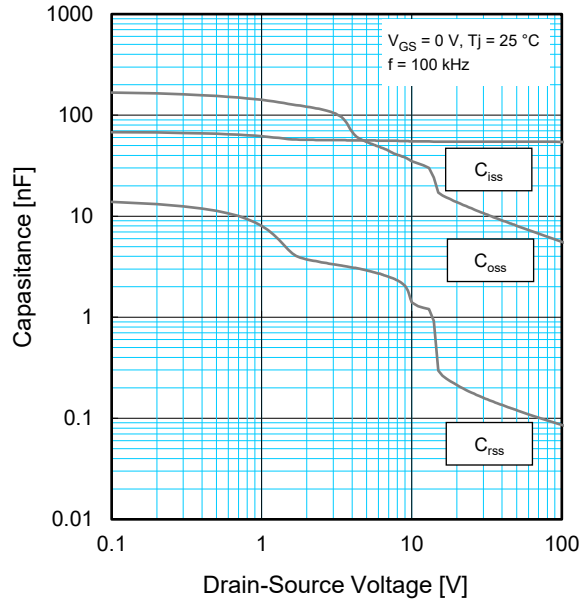
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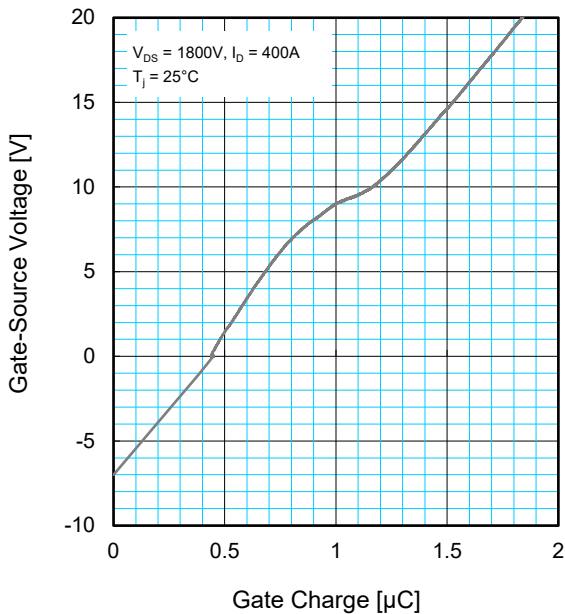
FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



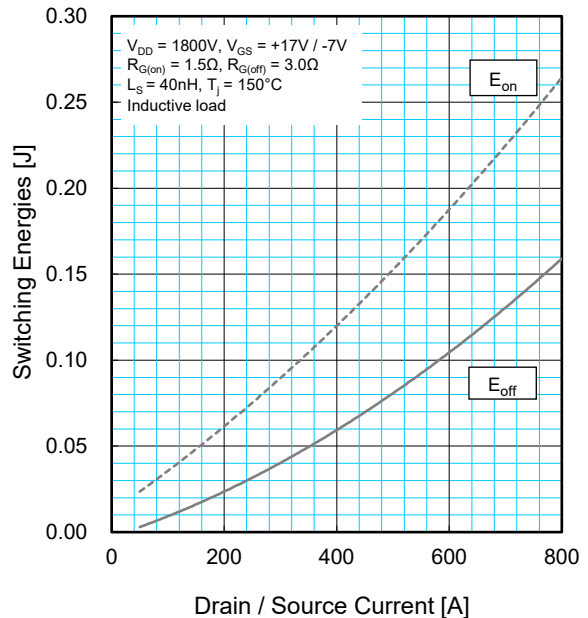
CAPACITANCE CHARACTERISTICS (TYPICAL)



GATE CHARGE CHARACTERISTICS (TYPICAL)



HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)



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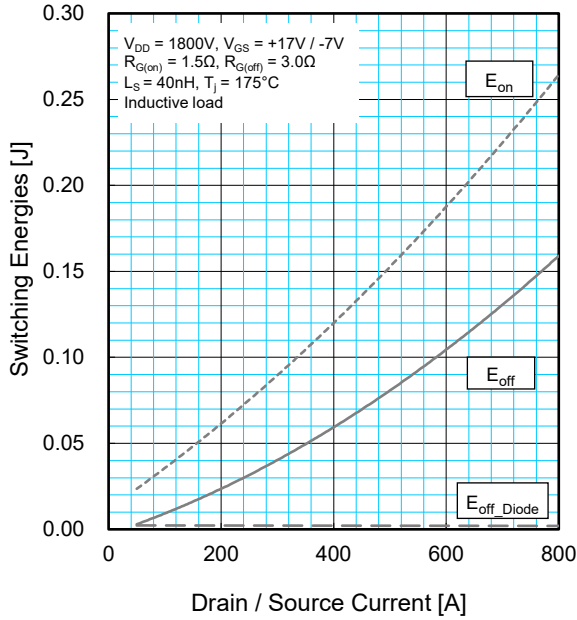
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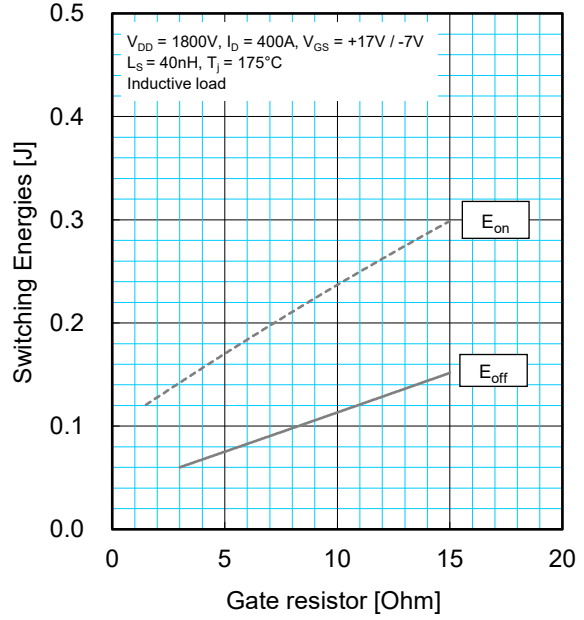
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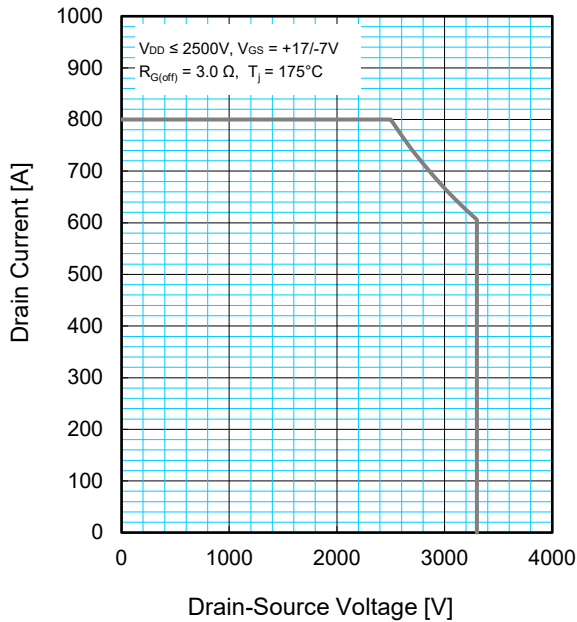
HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)



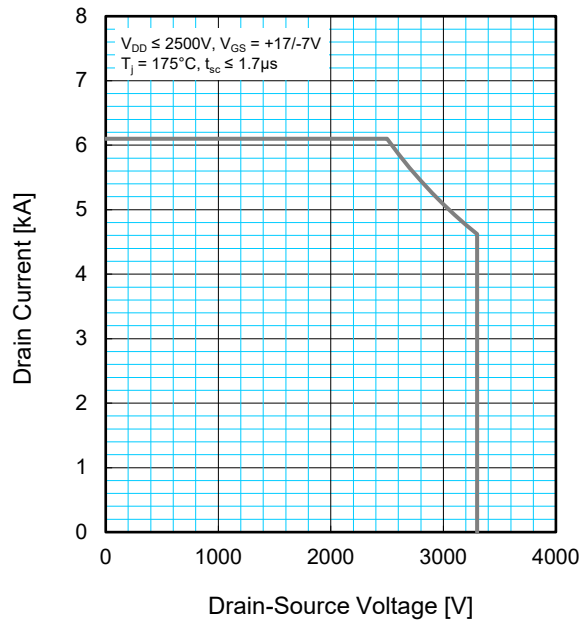
HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)



REVERSE BIAS SAFE OPERATING AREA (RBSOA)



SHORT CIRCUIT SAFE OPERATING AREA (SCSOA)



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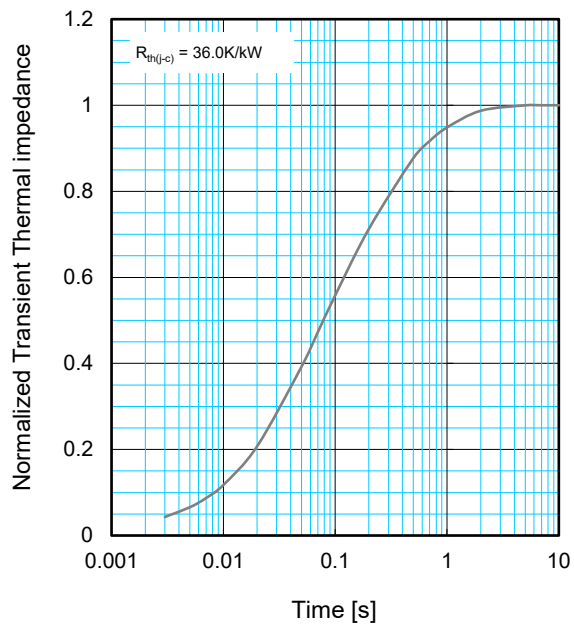
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PERFORMANCE CURVES

TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS



$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i \left\{ 1 - \exp\left(-\frac{t}{\tau_i}\right) \right\}$$

	1	2	3	4
R_i / R_{th} :	0.0078	0.1975	0.3553	0.4393
τ_i [sec.] :	0.0001	0.7324	0.0381	0.1698

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